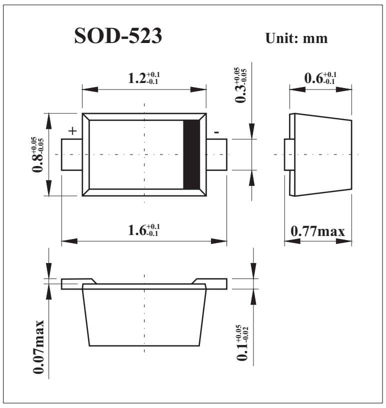
TY Semicondutor®

Product specification

1PS79SB10



■ Features

- Low forward voltage
- Guard ring protected
- Ultra small plastic SMD package.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
continuous reverse voltage	V_R	30	V
continuous forward current	I_F	200	mA
repetitive peak forward current *	I_{FRM}	300	mA
non-repetitive peak forward current tp < 10 ms	I_{FSM}	600	mA
operating ambient temperature	T_{amb}	-65 to 125	℃
thermal resistance from junction to ambient	R_{thj-a}	450	K/W
junction temperature	T_j	125	℃
storage temperature	T_{stg}	-65 to 150	℃

* tp ≤ 1 s; d ≤ 0.5

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
continuous forward voltage	V_F	I_F = 0.1 mA			240	mV
		I_F = 1 mA			320	mV
		I_F = 10 mA			400	mV
		I_F = 30 mA			500	mV
		I_F = 100 mA			800	mV
continuous reverse current	I_R	V_R = 25 V *			2	μA
diode capacitance	C_d	V_R = 1 V; f = 1 MHz			10	pF

* Pulsed test: tp = 300 μs; δ = 0.02.

■ Marking

Marking	F